

## TITLE OF THE INVENTION

Polishing Pads Useful in Chemical Mechanical Polishing  
of Substrates in the Presence of a Slurry  
Containing Abrasive Particles

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## CROSS REFERENCE TO RELATED APPLICATIONS

This application claims the benefit under 35 U.S.C. §  
112(e) of U.S. Provisional Application No. 60/129,048,  
filed April 13, 1999, the entire disclosure of which is  
10 incorporated herein by reference.

*PS 2/25/05* This application ~~claims the benefit under 35 U.S.C. §~~  
~~112(e)~~ <sup>is a con</sup> of U.S. Patent Application No. 09/545,982, filed on  
April 10, 2000, the entire disclosure of which is  
incorporated herein by reference.

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STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH OR  
DEVELOPMENT

- N/A -

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## BACKGROUND OF THE INVENTION

Semiconductor devices are formed from a flat, thin  
wafer of a semiconductor material, such as silicon. The  
wafer must be polished to achieve a sufficiently flat  
surface with no or minimal defects. A variety of chemical,  
25 electrochemical, and chemical mechanical polishing  
techniques are employed to polish the wafers.

In chemical mechanical polishing ("CMP"), a polishing  
pad made of a urethane material is used in conjunction  
with a slurry to polish the wafers. The slurry comprises  
30 abrasive particles, such as aluminum oxide, cerium oxide,  
or silica particles, dispersed in an aqueous medium. The  
abrasive particles generally range in size from 100 to